

Postdoc position for Molecular Beam Epitaxy of III-nitrides

A postdoctoral research position in Molecular Beam epitaxy of III-nitride semiconductors is available at the **Microelectronics Research Group (MRG) of IESL, FORTH**, at Heraklion, Crete, Greece.

<http://www.iesl.forth.gr/research/material/mrg/>

The position is immediately available and an appropriate candidate is expected to work until the end of October 2011. The postdoctoral fellow will undertake research for the heteroepitaxy of III-Nitride semiconductors on novel substrates and the growth of nanopillar and quantum dot structures by nitrogen RF plasma source molecular beam epitaxy (RF-MBE).

Strong expertise in RF-MBE growth, High Resolution X-ray Diffraction and physics of III-Nitride semiconductors or other wurtzite semiconductor materials is highly desirable.

Expressions of interest-applications are invited for immediate appointment.

Applicants should provide by email the following:

- (1) Expression-of-interest letter describing research interests and experience
- (2) Analytic curriculum vitae
- (3) Three reference names

For more information and applications contact:

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